

Docket No. 0057-2534-2YY DIV

IN RE APPLICATION OF: Shuichi UENO, et al.

SERIAL NO: 09/429,283

FILED: OCTOBER 28, 1999

FOR: SEMICONDUCTOR DEVICE AND METHOD OF MANUFACTURING THE SAME

"RESPONSE UNDER 37 CFR 1.116-
EXPEDITED PROCEDURE EXAMINING
GROUP 3723"

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Transmitted herewith is an amendment in the above-identified application.

- ☒ No additional fee is required
- ☐ Small entity status of this application under 37 C.F.R. §1.9 and §1.27 is claimed.
- ☒ Additional documents filed herewith: Marked-up copy

The Fee has been calculated as shown below:

CLAIMS	CLAIMS REMAINING		HIGHEST NUMBER PREVIOUSLY PAID	NO. EXTRA CLAIMS	RATE	CALCULATIONS
TOTAL	14	MINUS	20	0	× \$18 =	\$0.00
INDEPENDENT	3	MINUS	3	0	× \$80 =	\$0.00
		<input type="checkbox"/> MULTIPLE DEPENDENT CLAIMS			+ \$270 =	\$0.00
		TOTAL OF ABOVE CALCULATIONS				\$0.00
		<input type="checkbox"/> Reduction by 50% for filing by Small Entity				\$0.00
		<input type="checkbox"/> Recordation of Assignment			+ \$40 =	\$0.00
		TOTAL				\$0.00

- ☐ A check in the amount of _____ is attached.
- ☒ Please charge any additional Fees for the papers being filed herewith and for which no check is enclosed herewith, or credit any overpayment to deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.
- ☒ If these papers are not considered timely filed by the Patent and Trademark Office, then a petition is hereby made under 37 C.F.R. §1.136, and any additional fees required under 37 C.F.R. §1.136 for any necessary extension of time may be charged to Deposit Account No. 15-0030. A duplicate copy of this sheet is enclosed.

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0057-2534-2YY DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :
SHUICHI UENO ET AL : EXAMINER: FOURSON
SERIAL NO: 09/429,283 ✓ :
FILED: OCTOBER 28, 1999 : GROUP ART UNIT: 2823
FOR: SEMICONDUCTOR DEVICE AND :
METHOD OF MANUFACTURING
THE SAME :

AMENDMENT UNDER 37 C.F.R. §1.116

ASSISTANT COMMISSIONER FOR PATENTS
WASHINGTON, D.C. 20231

SIR:

Responsive to the Office Action dated February 13, 2001, please amend the above-identified application as follows:

IN THE SPECIFICATION

Please substitute the following paragraph for the paragraph at page 67, line 1. A marked up copy is provided in the attachment.

--In Table 5, impurity doses for forming the gate electrodes of the N-channel transistors T41, T42 and T43 are equally $5 \times 10^{15}/\text{cm}^2$. Phosphorus (P) is implanted as an impurity for each electrode with the implantation energy of 30 keV.--

to be
entered
(8/21/9/01)

C1